MICRON.009DV1



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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Schuegraf et al.) Group Art Unit 2811
Appl. No.	:	08/932,228) I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class
Filed	:	September 17, 1997	mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on
For	:	SHALLOW TRENCH ISOLATION USING LOW DIELECTRIC CONSTANT INSULATOR	August 29, 2000 (Date) Adeel S. Akhtar, Reg. No. 41,394
Examiner	:	Hung Vu)

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

ant Commissioner for Patents
ngton, D.C. 20231

The sponse to the Final Office Action mailed June 29, 2000, in the above-captioned ation, Applicants respectfully. application, Applicants respectfully request entry of the amendment below and reconsideration of the rejections in view of the remarks below.

IN THE CLAIMS:

- (Twice Amended) An isolation structure in a semiconductor substrate comprising: 11.
- a recessed portion formed [therein in] with a vertical sidewall within the semiconductor substrate; and
- a dielectric material comprising a halide-doped silicon oxide filling the recessed portion, said dielectric material having a dielectric constant lower than the dielectric constant of silicon dioxide.